

MGFS45A2527B

2.5 - 2.7GHz BAND 32W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFS45A2527B is an internally impedance-matched GaAs power FET especially designed for use in 2.5 - 2.7 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

- Class A operation
- Internally matched to 50(ohm) system
- High output power
P1dB = 32W (TYP.) @ f=2.5 - 2.7 GHz
- High power gain
GLP = 12 dB (TYP.) @ f=2.5 - 2.7GHz
- High power added efficiency
P.A.E. = 40 % (TYP.) @ f=2.5 - 2.7GHz
- 3rd order IM distortion
IM = -45dBc (TYP.) @ f=2.5 - 2.7GHz

APPLICATION

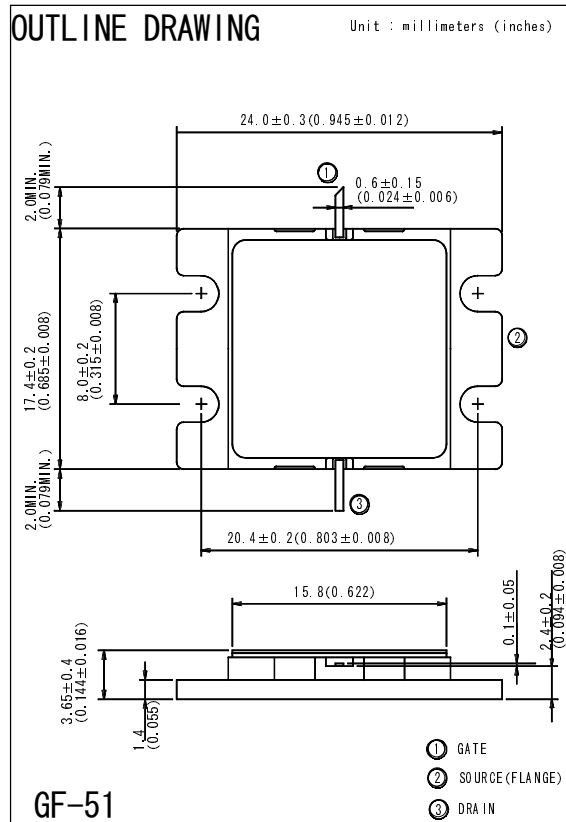
- item 01 : 2.5 - 2.7 GHz band power amplifier
- item 51 : 2.5 - 2.7 GHz band digital ratio communication

QUALITY GRADE

GG

RECOMMENDED BIAS CONDITIONS

- VDS = 10 (V)
- ID = 6.5 (A)
- RG=25 (ohm)



ABSOLUTE MAXIMUM RATINGS

(Ta=25deg.C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain voltage	-20	V
VGSO	Gate to source voltage	-10	V
PT *1	Total power dissipation	107	W
Tch	Channel temperature	175	deg.C
Tstg	Storage temperature	-65 / +175	deg.C

*1 : Tc=25deg.C

< Keep safety first in your circuit designs! >
Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (1)placement of substitutive, auxiliary circuits, (2)use of non-flammable material or (3)prevention against any malfunction or mishap.

ELECTRICAL CHARACTERISTICS

(Ta=25deg.C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
VGS(off)	Gate to source cut-off voltage	VDS = 3V , ID = 84mA	-	-	-5	V
P1dB	Output power	VDS=10V, ID(RF off)=6.5A, f=2.5 - 2.7GHz	44	45	-	dBm
GLP	Linear power gain		11	12	-	dB
ID	Drain current		-	7.5	-	A
P.A.E.	Power added efficiency		-	40	-	%
IM3 *2	3rd order IM distortion		-42	-45	-	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	1.2	1.4	deg.C/W

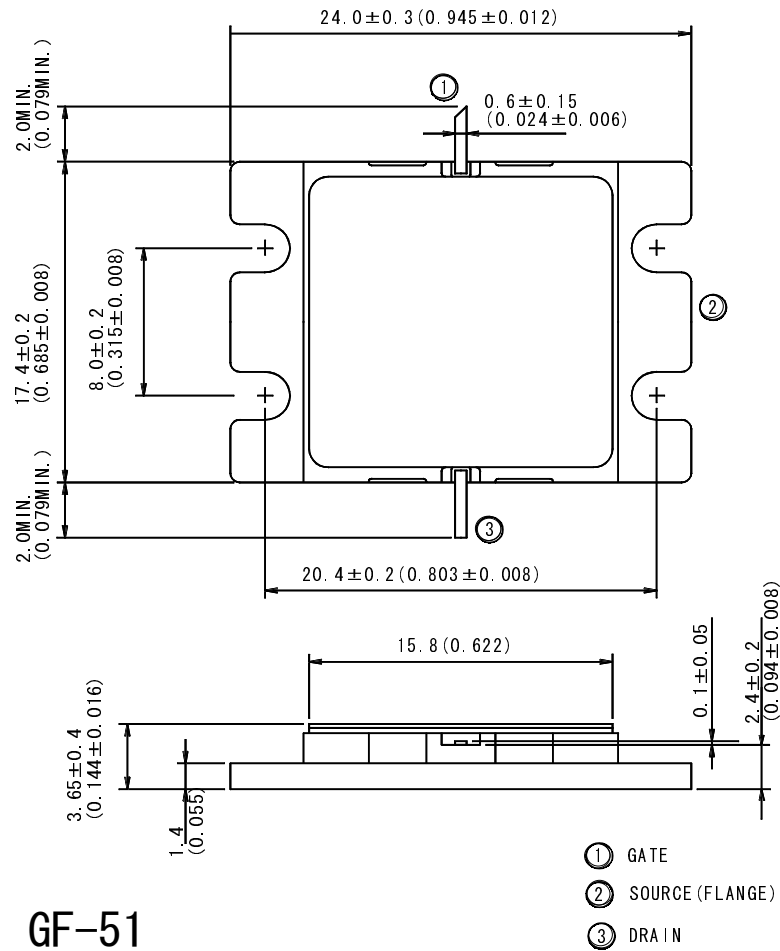
*2 : item -51,2 tone test, Po=34.5dBm Single Carrier Level, f=2.5, 2.6, 2.7GHz, delta f=5MHz

*3 : Channel-case

S-band 30W Power GaAs FET

OUTLINE DRAWING

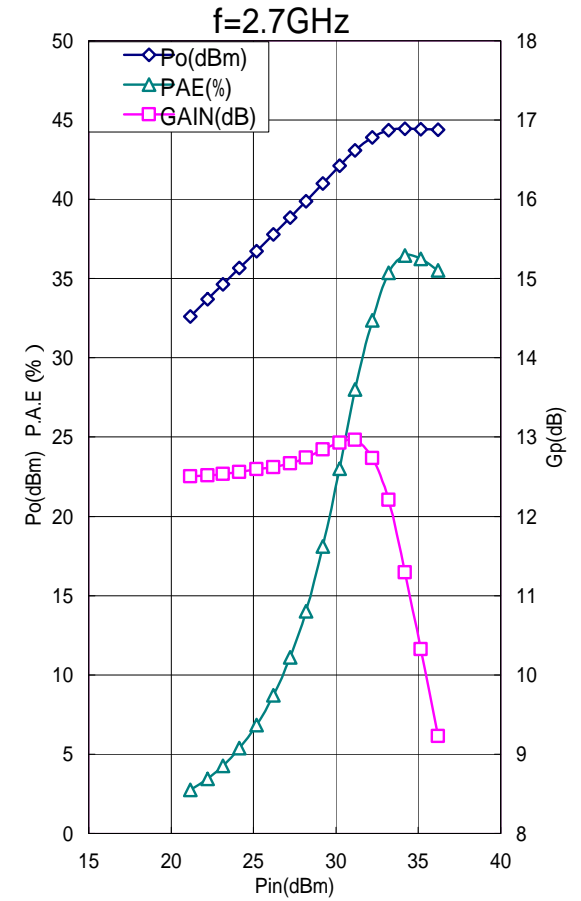
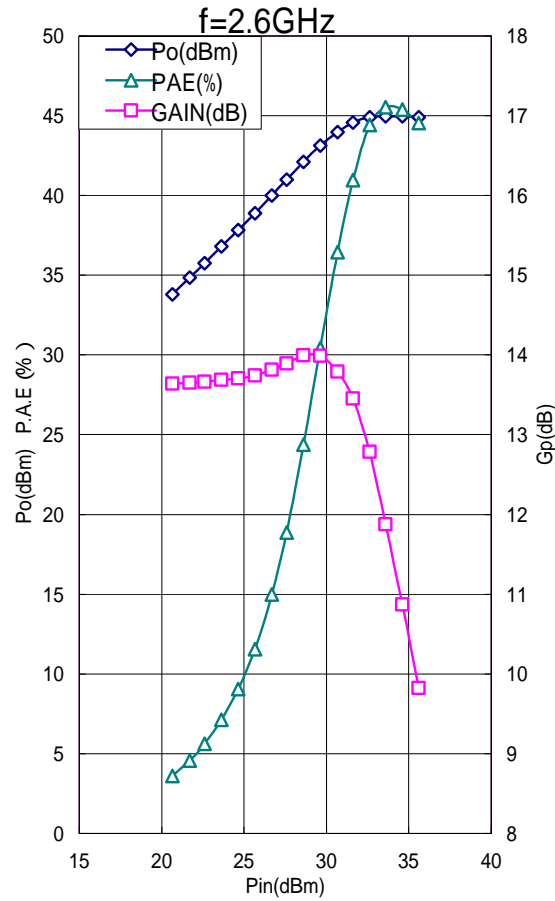
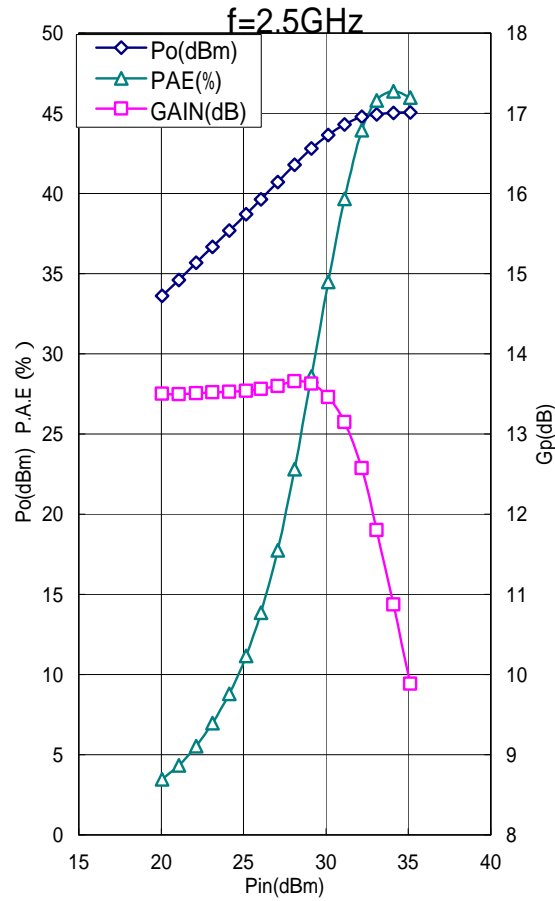
Unit : millimeters (inches)



GF-51

S-band 30W Power GaAs FET MGFS45A2527B

OUTPUT POWER & POWER ADDED EFFICIENCY vs. INPUT POWER



S-band 30W Power GaAs FET MGFS45A2527B

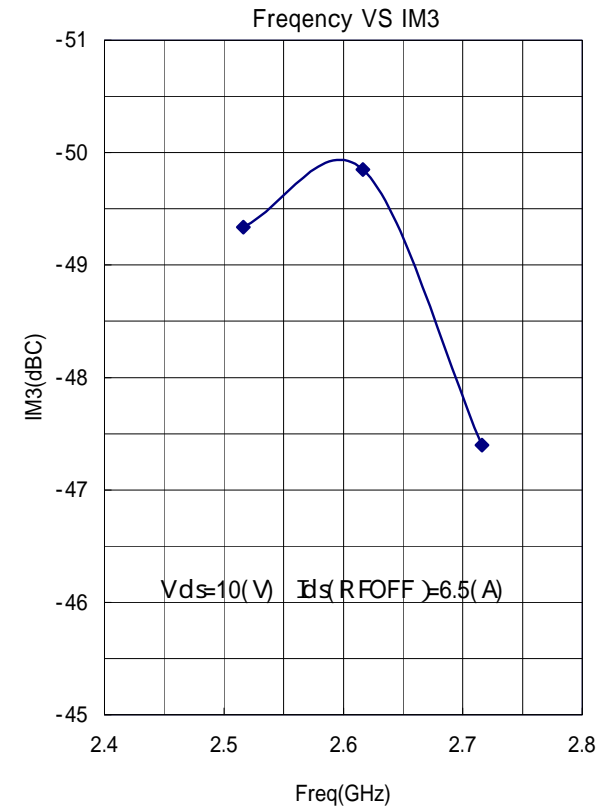
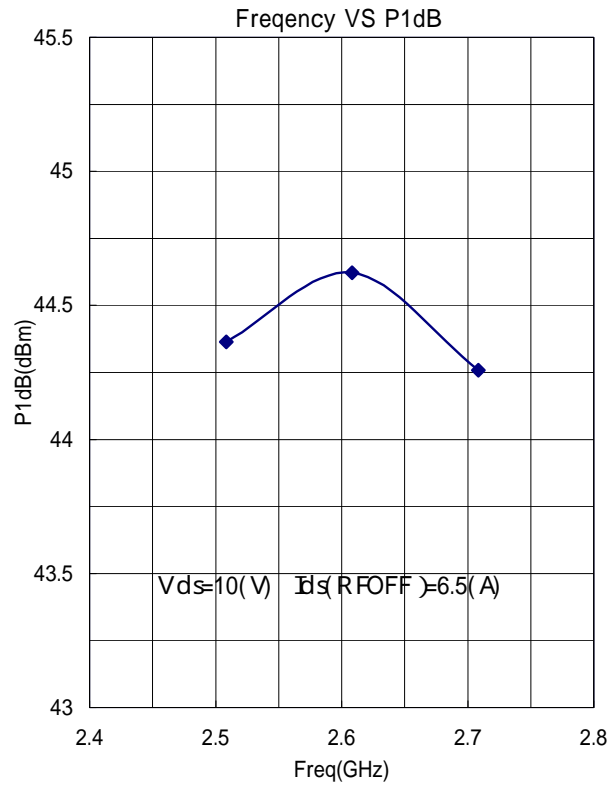
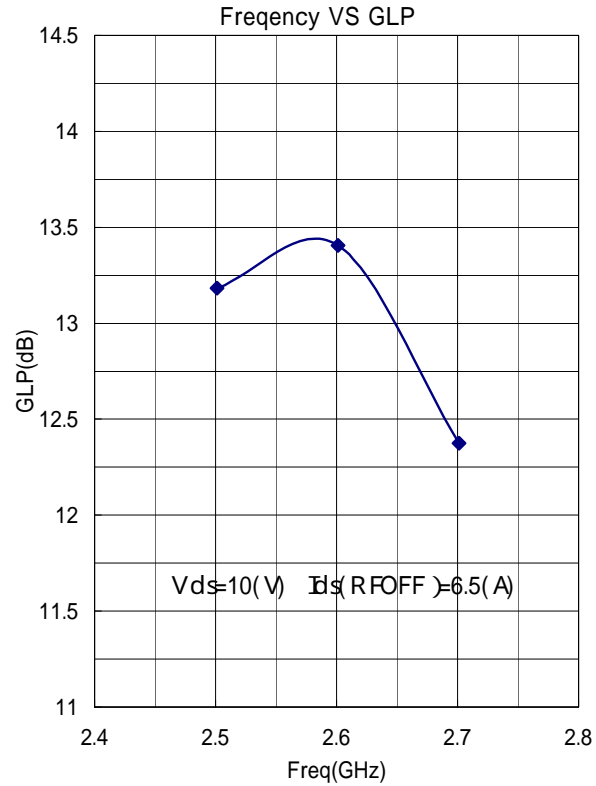
S PARAMETERES(T=25deg.C,VDS=10V,ID=6.5A)

Freq	S11		S21		S12		S22	
	(mag)	(ang)	(mag)	(ang)	(mag)	(ang)	(mag)	(ang)
2.00	0.88	74.01	1.42	-115.63	0.01	-79.30	0.79	101.57
2.05	0.87	67.63	1.56	-124.88	0.01	-86.26	0.77	95.64
2.10	0.85	60.94	1.72	-134.47	0.01	-102.29	0.75	89.25
2.15	0.82	53.50	1.91	-144.48	0.01	-111.11	0.73	83.20
2.20	0.79	45.38	2.12	-155.53	0.01	-129.00	0.70	75.83
2.25	0.76	36.25	2.38	-167.27	0.01	-140.42	0.67	67.92
2.30	0.72	26.06	2.66	-179.79	0.01	-159.19	0.64	58.86
2.35	0.66	14.95	2.99	166.21	0.02	176.25	0.59	47.67
2.40	0.59	1.86	3.34	150.86	0.02	155.14	0.54	34.08
2.45	0.51	-13.16	3.70	133.43	0.02	126.07	0.48	16.39
2.50	0.40	-31.23	4.01	115.11	0.02	98.68	0.43	-5.01
2.55	0.28	-51.53	4.24	95.76	0.02	71.43	0.39	-31.79
2.60	0.16	-78.16	4.32	75.62	0.02	43.53	0.38	-61.12
2.65	0.07	-146.41	4.27	55.31	0.02	15.41	0.40	-87.87
2.70	0.12	127.83	4.09	35.45	0.03	-11.45	0.45	-109.18
2.75	0.22	95.47	3.80	16.42	0.03	-33.34	0.49	-125.33
2.80	0.30	74.56	3.51	-1.65	0.03	-54.63	0.53	-137.70
2.85	0.38	56.47	3.18	-19.06	0.03	-75.33	0.57	-147.32
2.90	0.45	40.38	2.88	-35.49	0.03	-94.35	0.60	-154.95
2.95	0.51	24.35	2.58	-51.73	0.03	-111.68	0.62	-161.21
3.00	0.58	8.80	2.30	-67.16	0.03	-126.90	0.64	-166.56

This S-Parameter data show measurements performed on each single-ended FET

S-band 30W Power GaAs FET MGFS45A2527B

Frequency characteristic



MGFS45A2527B**2.5 - 2.7GHz BAND 32W INTERNALLY MATCHED GaAs FET****Requests Regarding Safety Designs**

Mitsubishi Electric constantly strives to raise the level of its quality and reliability. Despite these concerted efforts, however, there will be occasions when our semiconductor products suffer breakdowns, malfunctions or other problems. In view of this reality, it is requested that every feasible precaution be taken in the pursuit of redundancy design, malfunction prevention design and other safety-related designs, to prevent breakdowns or malfunctions in our products from resulting in accidents involving people, fires, social losses or other problems, thereby upholding the highest levels of safety in the products when in use by customers.

Matters of Importance when Using these Materials

1. These materials are designed as reference materials to ensure that all customers purchase Mitsubishi Electric semiconductors best suited to their specific use applications. Please be aware, however, that the technical information contained in these materials does not comprise consent for the execution or use of intellectual property rights or other rights owned by Mitsubishi Electric Corporation.
2. Mitsubishi Electric does not assume responsibility for damages resulting from the use of product data, graphs, charts, programs, algorithms or other applied circuit examples described in these materials, or for the infringement of the rights of third-party owners resulting from such use.
3. The data, graphs, charts, programs, algorithms and all other information described in these materials were current at the issue of these materials, with Mitsubishi Electric reserving the right to make any necessary updates or changes in the products or specifications in these materials without prior notice. Before purchasing Mitsubishi Electric semiconductor products, therefore, please obtain the latest available information from Mitsubishi Electric directly or an authorized dealer.
4. Every possible effort has been made to ensure that the information described in these materials is fully accurate. However, Mitsubishi Electric assumes no responsibility for damages resulting from inaccuracies occurring within these materials.
5. When using the product data, technical contents indicated on the graphs, charts, programs or algorithms described in these materials, assessments should not be limited to only the technical contents, programs and algorithm units. Rather, it is requested that ample evaluations be made of each individual system as a whole, with the customer assuming full responsibility for decisions on the propriety of application. Mitsubishi Electric does not accept responsibility for the propriety of application.
6. The products described in these materials, with the exception of special mention concerning use and reliability, have been designed and manufactured with the purpose of use in general electronic machinery. Accordingly these products have not been designed and manufactured with the purpose of application in machinery or systems that will be used under conditions that can affect human life, or in machinery or systems used in social infrastructure that demand a particularly high degree of reliability. When considering the use of the products described in these materials in transportation machinery (automobiles, trains, vessels), for objectives related to medical treatment, aerospace, nuclear power control, submarine repeaters or systems or other specialized applications, please consult with Mitsubishi Electric directly or an authorized dealer.
7. When considering use of products for purposes other than the specific applications described in these materials, please inquire at Mitsubishi Electric or an authorized dealer.
8. The prior consent of Mitsubishi Electric in writing is required for any reprinting or reproduction of these materials.
9. Please direct any inquiries regarding further details of these materials, or any other comments or matters of attention, to Mitsubishi Electric or an authorized dealer.